

**Amendments to the Specification**

Please replace the paragraph beginning on page 16, line 9 with the following amended paragraph:

ESD implantation is usually performed after the gate structure is finished. Fig. 25 depicts ESD implantation as indicated with the arrows and the formation of a P-ESD or [N-DSD] N-ESD layer 29a. A photoresistance layer 91 protects the regions that needn't be implanted. The two gate structures also serve as two shields defining the area to be implanted.